

900V 9A 1.28Ω N-ch Power MOSFET

Description

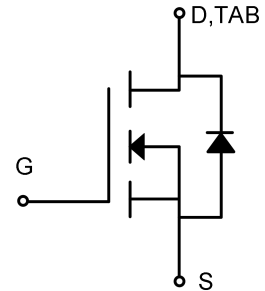
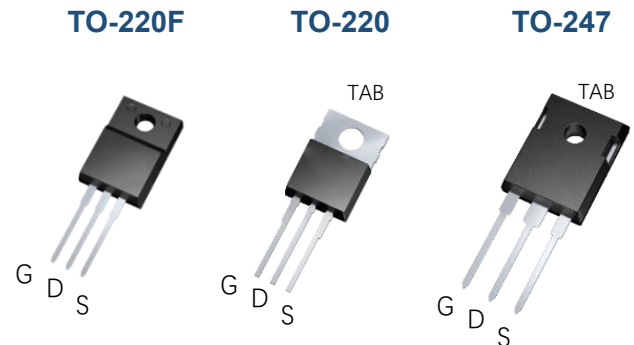
WMOS™ D1 is Wayon's 1st generation VDMOS family that is dramatic reduction in on-resistance and ultra-low gate charge for applications requiring high power density and high efficiency. And it is very robust and RoHS compliant.

Features

- Typ. $R_{DS(on)}=1.28\Omega@V_{GS}=10V$
- 100% avalanche tested
- Pb-free, Halogen free

Applications

- SMPS
- Charger
- DC-DC



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	WML9N90D1	WMK9N90D1	WMJ9N90D1	Unit
Drain-source voltage	V_{DSS}		900		V
Gate-source voltage	V_{GS}		± 30		V
Continuous drain current	I_D		9		A
Pulsed drain current	I_{DM}		36		A
Avalanche energy, single pulse	E_{AS}		900		mJ
Power dissipation	P_D	62.5	201	215	W
Derate above 25°C		0.5	1.6	1.72	W/°C
Operating junction temperature	T_j		-55~150		°C
Storage temperature	T_{stg}		-55~150		°C
Continuous diode forward current	I_S		9		A
Diode pulse current	I_{Spulse}		36		A

Thermal Characteristic

Thermal resistance, junction-to-case	$R_{\theta JC}$	2	0.62	0.58	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62.5	62.5	62.5	°C/W

Electrical Characteristics of MOSFET

				Min.	Typ.	Max.	
Drain-source break down voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	$T_C=25^\circ C$	900	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	$T_J=25^\circ C$	2	3.2	4	V
Drain-source leakage current	I_{DSS}	$V_{DS}=900V, V_{GS}=0V$	$T_J=25^\circ C$	-	-	1	μA
		$V_{DS}=720V, V_{GS}=0V$	$T_J=125^\circ C$	-	-	400	μA
Gate-source leakage current,forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	$T_J=25^\circ C$	-	-	100	nA
Gate-source leakage current,reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	$T_J=25^\circ C$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=4.5A$	$T_J=25^\circ C$	-	1.28	1.5	Ω
Transconductance	G_{fs}	$V_{DS}=20V$	$T_J=25^\circ C$	-	7.6	-	S

Dynamic Characteristics of MOSFET ($T_C=25^\circ C$)

				Min.	Typ.	Max.	
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V, V_{GS}=0V$		-	1700	-	pF
Output capacitance	C_{oss}			-	150	-	pF
Reverse transfer capacitance	C_{rss}			-	8	-	pF
Gate to source charge	Q_{gs}	$V_{DD}=450V$		-	11	-	nC
Gate to drain charge	Q_{gd}	$I_D=9A$		-	13	-	nC
Total gate charge	Q_g	$V_{GS}=0$ to 10V		-	38	-	nC

Switching Characteristics of MOSFET ($T_C=25^\circ C$)

				Min.	Typ.	Max.	
Turn-on delay time	$t_{d on}$	$V_{DS}=450V, I_D=9A, R_G=25\Omega,$ $V_{GS}=0$ to 10V		-	28	-	ns
Rise time	t_r			-	50	-	ns
Turn-off delay time	$t_{d off}$			-	100	-	ns
Fall time	t_f			-	48	-	ns

Characteristics of Body Diode ($T_C=25^\circ C$)

				Min.	Typ.	Max.	
Forward voltage	V_{SD}	$I_{SD}=9A, V_{GS}=0V$		-	-	1.4	V
Reverse recovery time	t_{rr}	$V_{DS}=450V, I_S=9A, V_{GS}=10V$ $-di/dt=100A/us$		-	496	-	ns
Reverse recovery current	I_{rr}			-	25	-	A
Recovery charge	Q_{rr}			-	6.2	-	μC

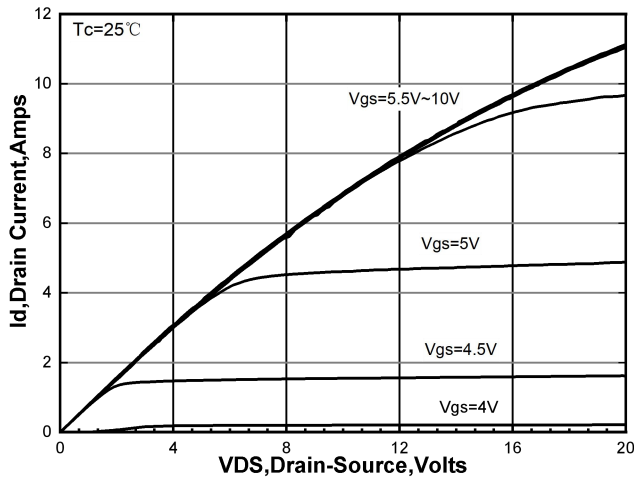


Figure 1. On-Region Characteristics

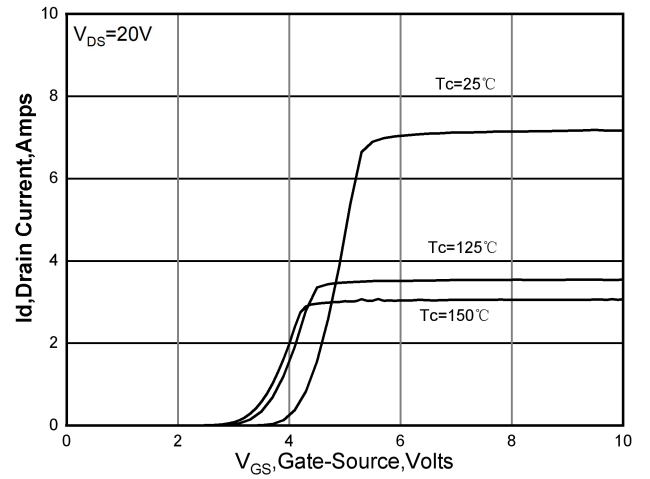


Figure 2. Transfer Characteristics

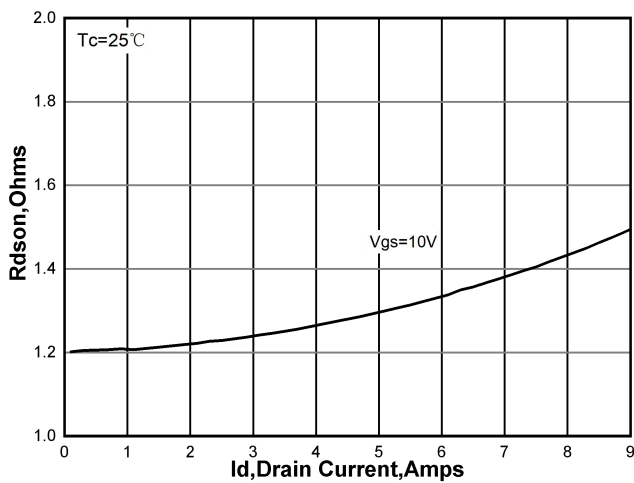


Figure 3. Static Drain-Source On Resistance

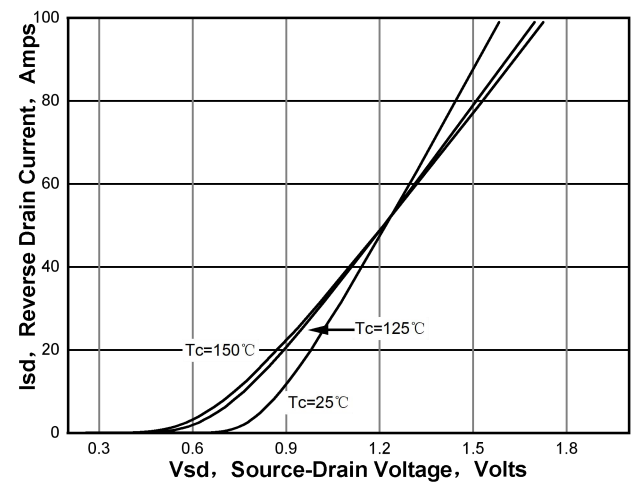


Figure 4. Typical Body Diode Transfer Characteristics

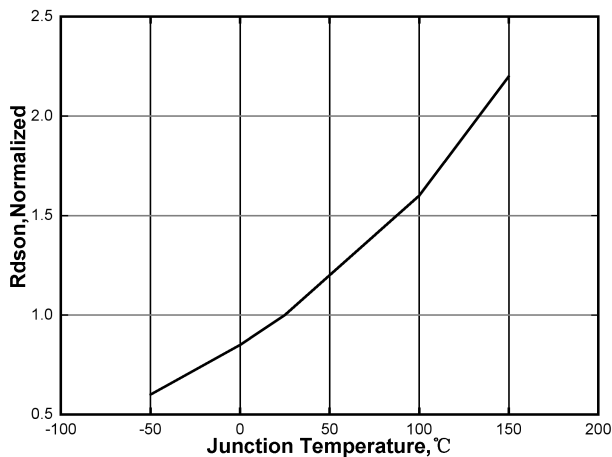


Figure 5. Normalized $R_{DS(on)}$ vs. Temperature

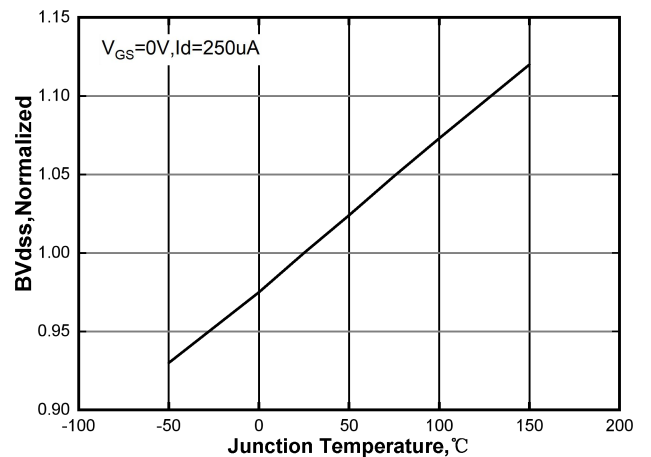


Figure 6. Normalized BV_{DSS} vs. Temperature

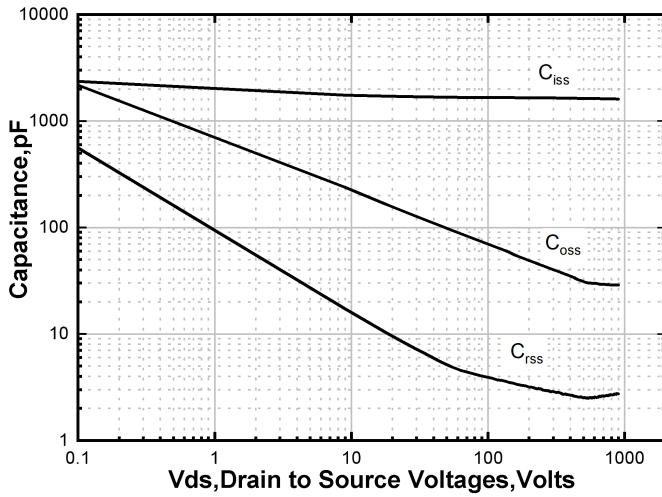


Figure 7. Capacitance Characteristics

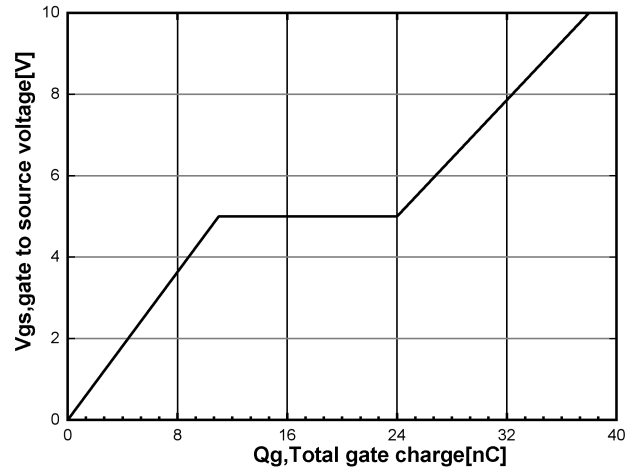


Figure 8. Gate Charge Characteristics

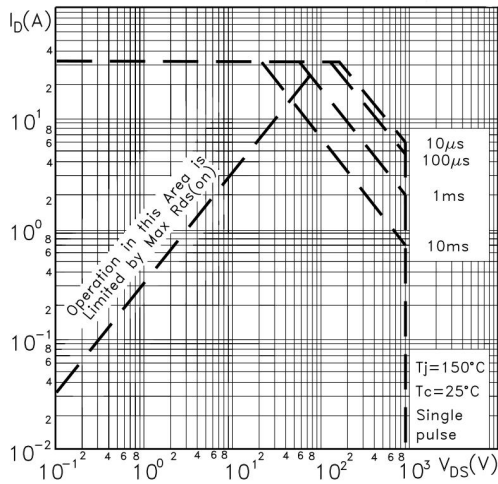


Figure 9. Maximum Safe Operating Area (TO-220F)

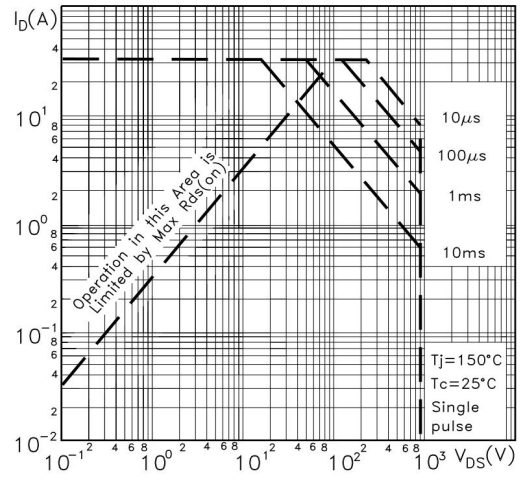


Figure 10. Maximum Safe Operating Area (TO-220)

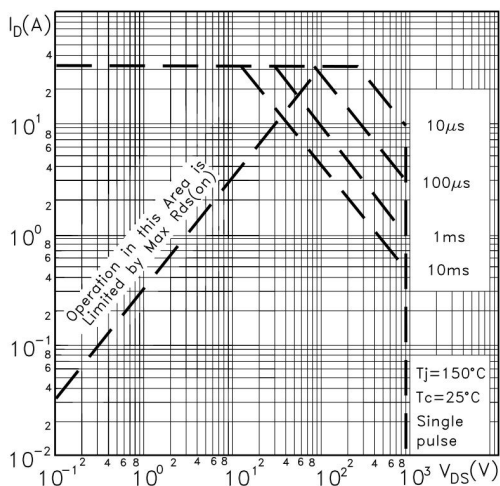
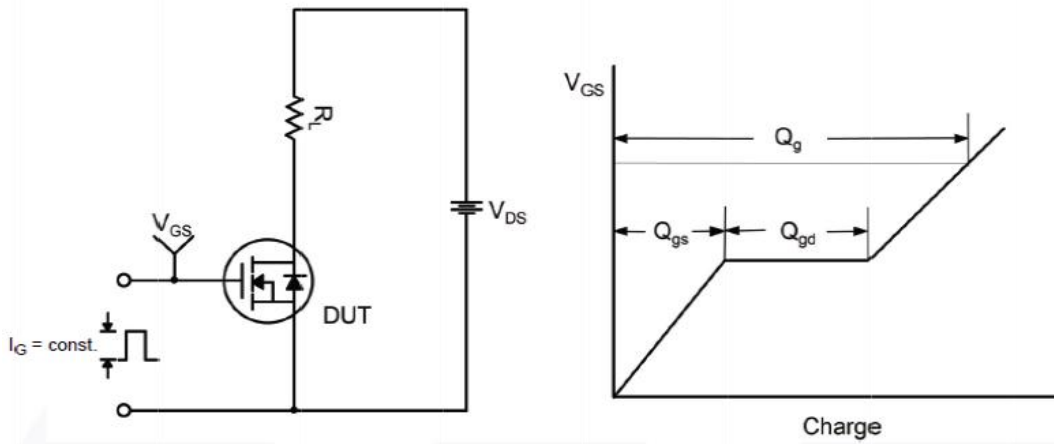
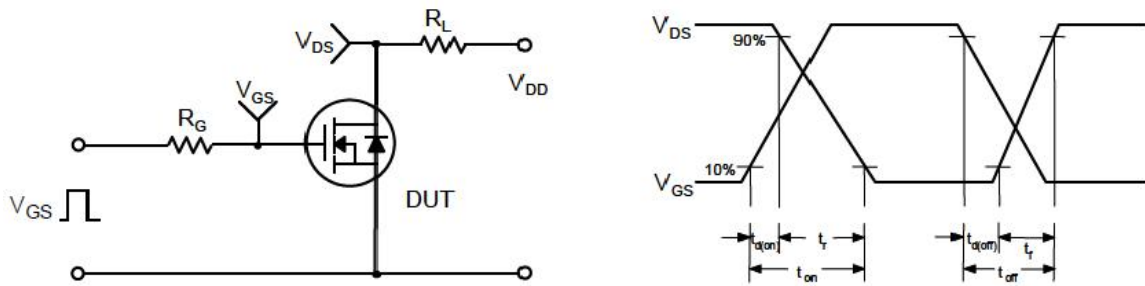


Figure 11. Maximum Safe Operating Area (TO-247)

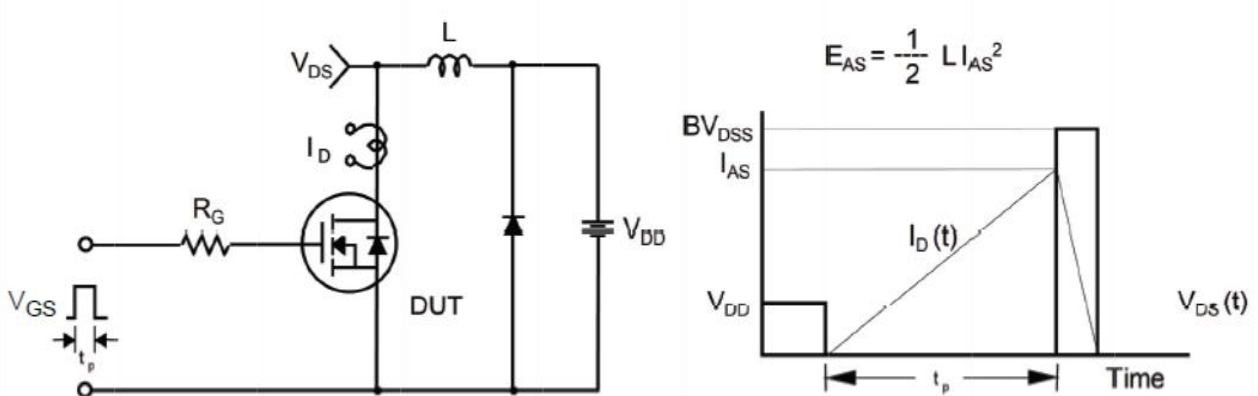
Gate Charge Test Circuit & Waveform



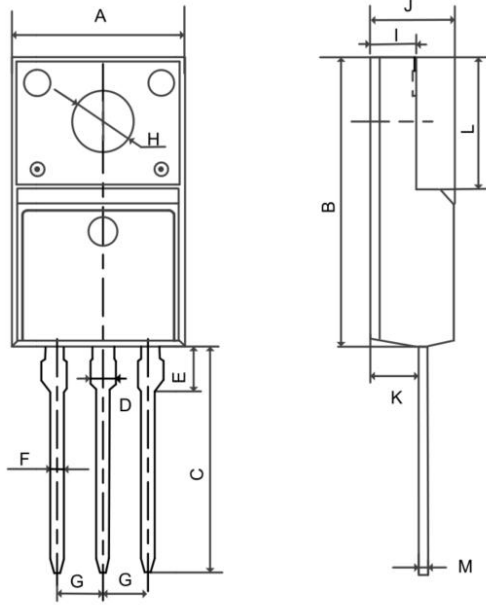
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



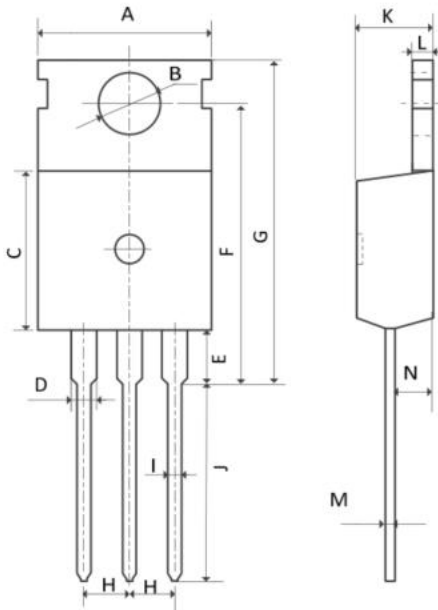
Mechanical Dimensions for TO-220F



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.67	16.07
C	12.70	13.30
D	1.12	1.32
E	1.85	2.15
F	0.59	0.79
G	2.39	2.69
H	3.08	3.29
I	2.34	2.74
J	4.50	4.90
K	2.61	2.91
L	6.50	6.90
M	0.40	0.60

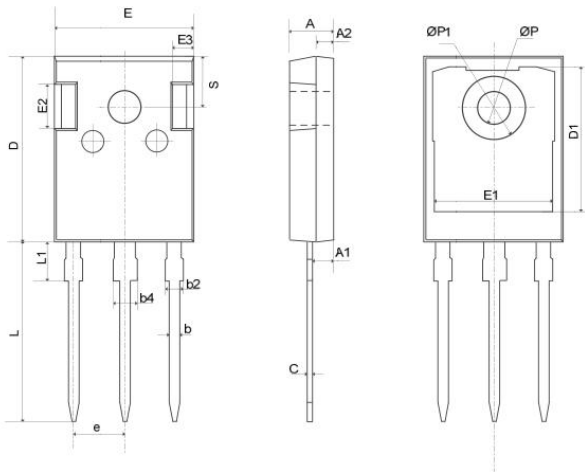
Mechanical Dimensions for TO-220



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.20
B	3.40	3.80
C	8.90	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Mechanical Dimensions for TO-247



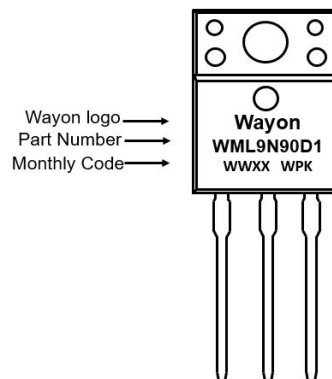
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.11	1.36
b2	1.91	2.21
b4	2.91	3.21
c	0.51	0.75
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.00	13.60
E2	4.80	5.20
E3	2.30	2.70
e	5.44BSC	
L	19.62	20.22
L1	—	4.30
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	

Ordering Information

Part	Package	Marking	Packing method
WML9N90D1	TO-220F	WML9N90D1	Tube
WMK9N90D1	TO-220	WMK9N90D1	Tube
WMJ9N90D1	TO-247	WMJ9N90D1	Tube

Marking Information




Contact Information

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For additional information, please contact your local Sales Representative.

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